

Product Summary

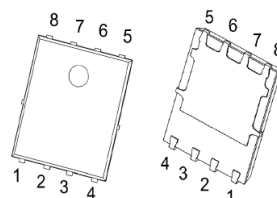
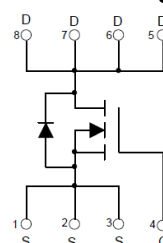
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	0.9m Ω @10V	200A

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Management
- Load Switching

PDFN5X6-8L

Schematic diagram

Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT008N04NNCUA	PDFN5X6-8L	T008N04NA	Reel & Tape	330mm	12mm	5000pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	200	A
	$T_C = 100^\circ\text{C}$		141	
Pulsed Drain Current ²		I_{DM}	800	A
Single Pulsed Avalanche Current ³		I_{AS}	68	A
Single Pulsed Avalanche Energy ³		E_{AS}	1156	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	166	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +175	$^\circ\text{C}$

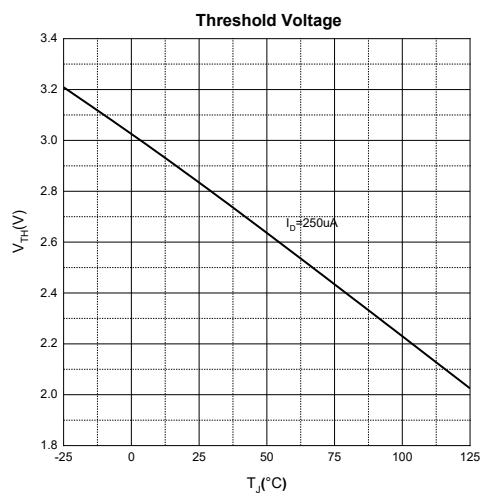
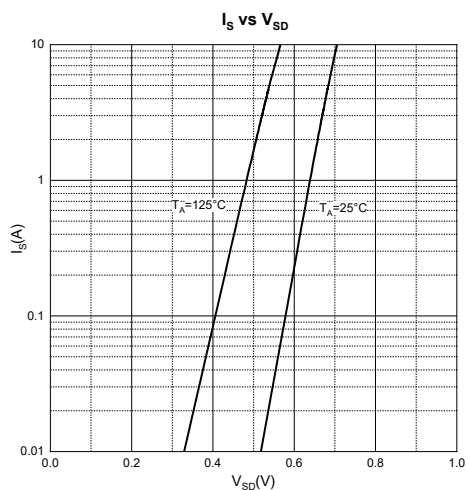
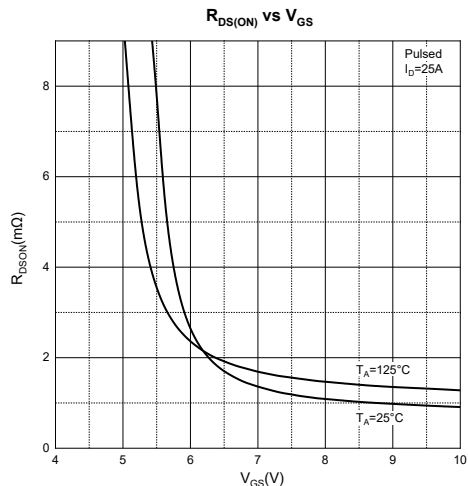
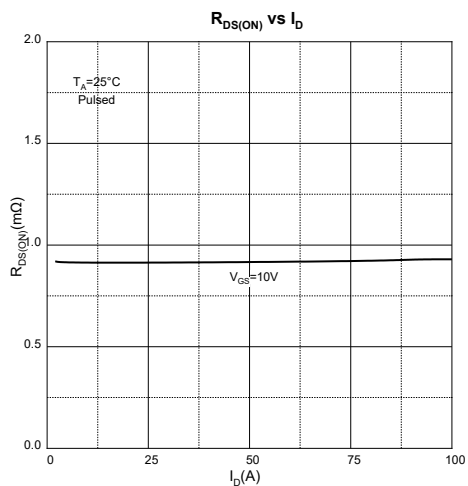
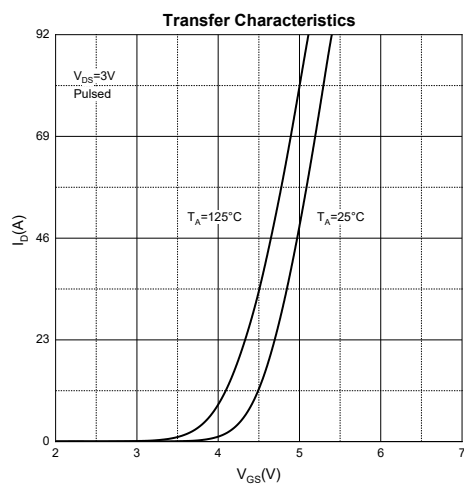
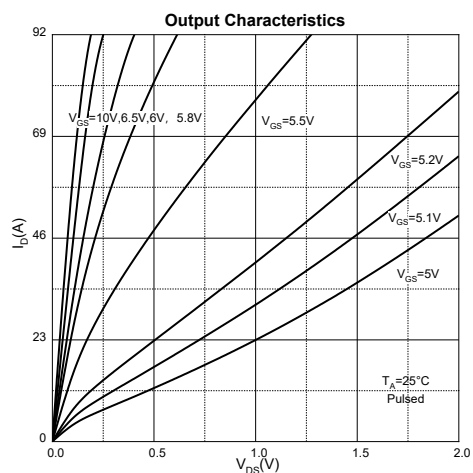
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

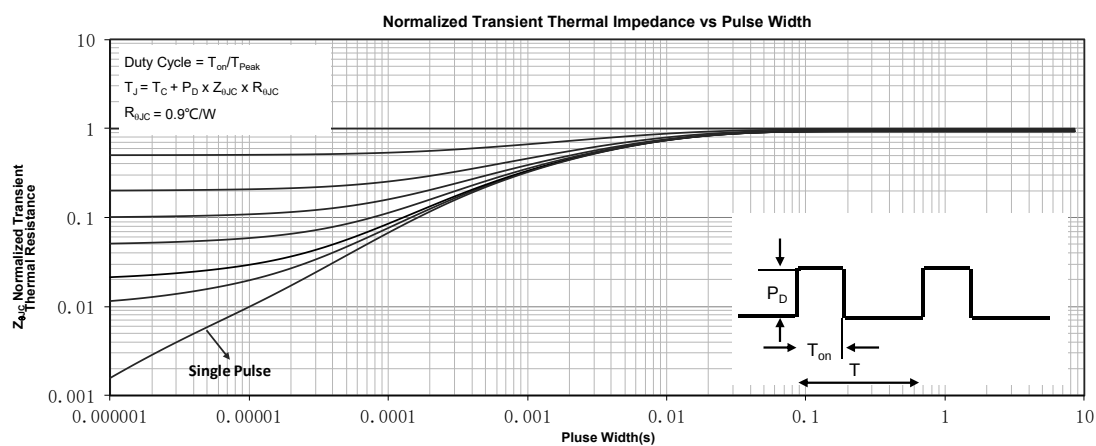
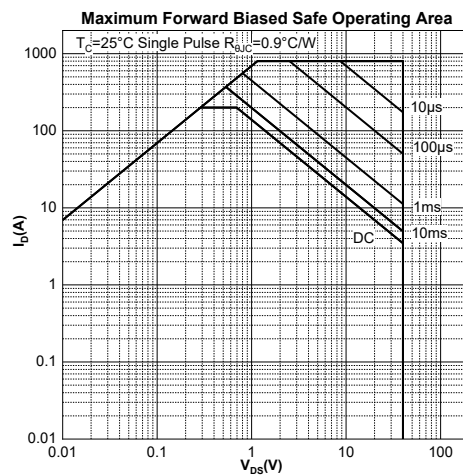
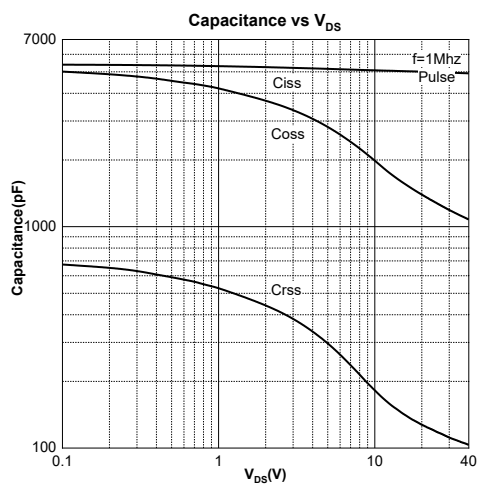
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.1	2.9	3.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 25A		0.9	1.1	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz		5137		pF
Output Capacitance	C _{oss}			1414		
Reverse Transfer Capacitance	C _{rss}			115		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		1.6		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 25V, V _{GS} = 10V, I _D = 25A		66		nC
Gate-Source Charge	Q _{gs}			24		
Gate-Drain Charge	Q _{gd}			10		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, R _G = 5Ω, R _L = 1.2Ω		20		ns
Turn-On Rise Time	t _r			27		
Turn-Off Delay Time	t _{d(off)}			40		
Turn-Off Fall Time	t _f			24		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V
Diode Continuous Forward Current ¹	I _S	T _C = 25°C			200	A
Diode Reverse Recovery Time	t _{rr}	I _F = 25A, dI/dt = 100A/μs		39		ns
Diode Reverse Recovery Charge	Q _{rr}			56		nC

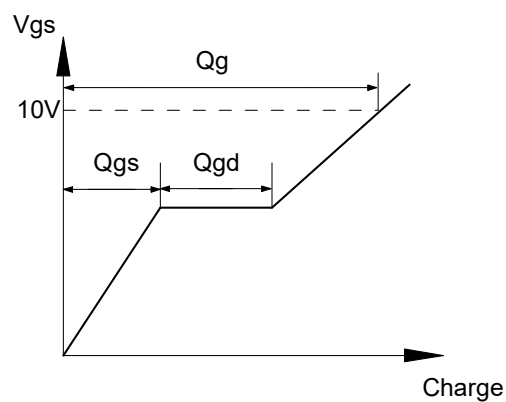
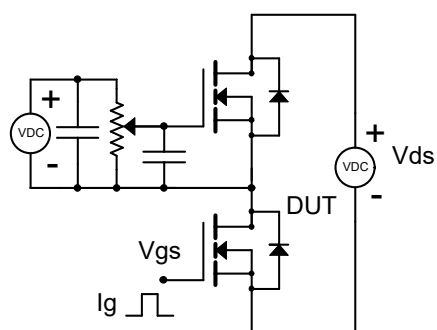
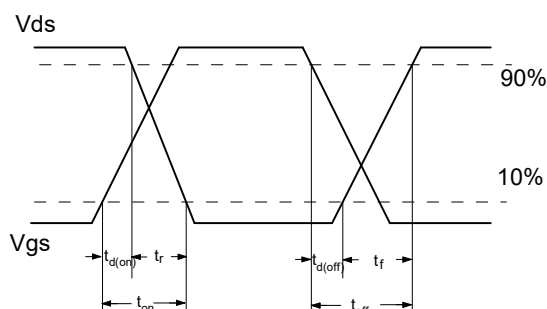
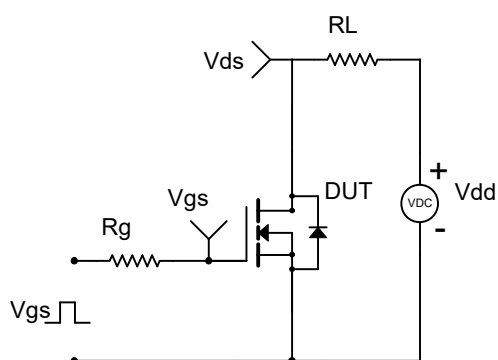
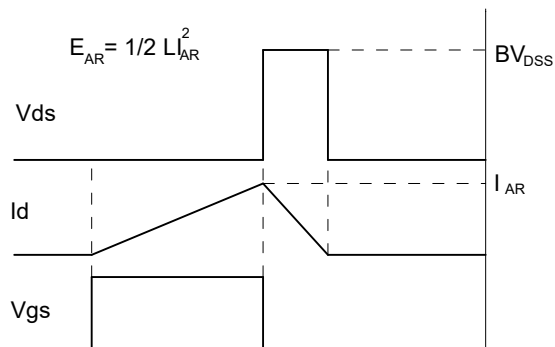
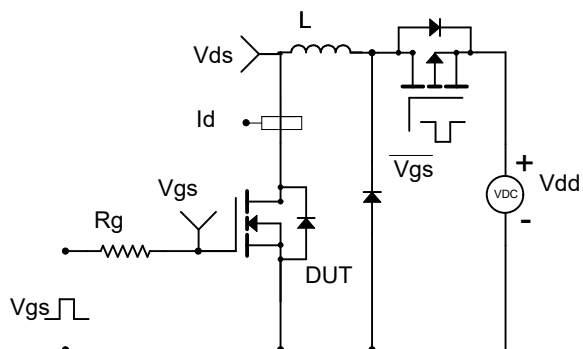
Notes:

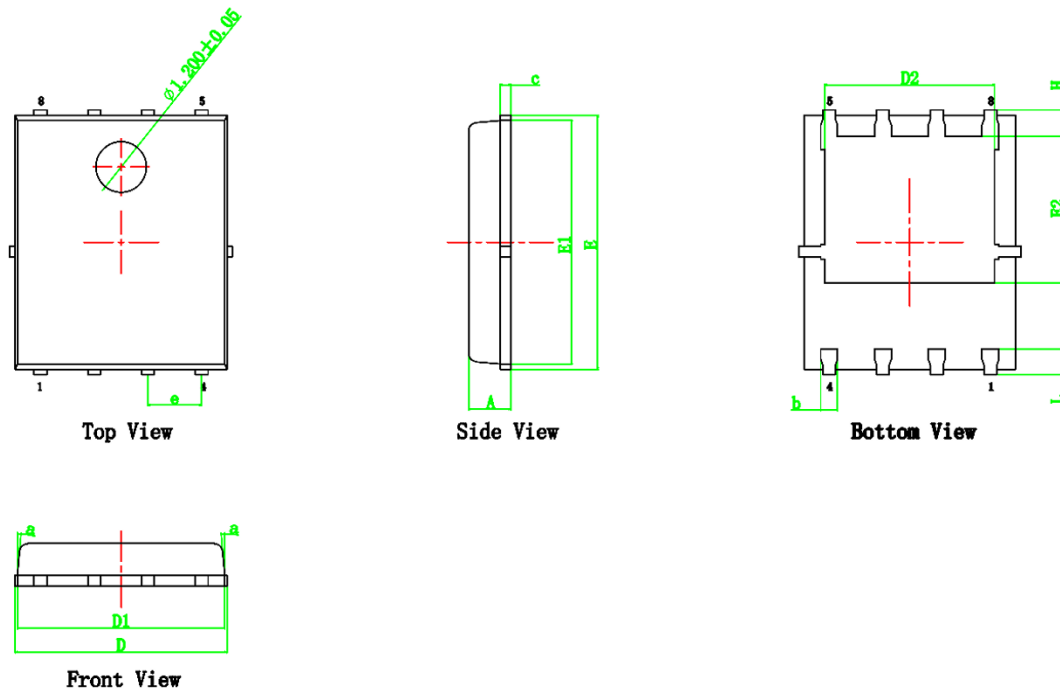
- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 40V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink.
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms


PDFN5X6-8L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.200	0.035	0.047
b	0.330	0.510	0.013	0.020
c	0.190	0.300	0.007	0.012
D	4.800	5.220	0.189	0.210
D2	3.900	4.300	0.154	0.170
E	5.900	6.100	0.232	0.240
E1	5.700	5.800	0.224	0.228
E2	3.350	3.750	0.132	0.148
e	1.270REF		0.050REF	
H	0.350	0.720	0.014	0.028
D1	4.800	5.000	0.189	0.197
L	0.350	0.750	0.014	0.030
a	0°	12°	0°	12°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.